

# SPECIFICATION

Device Name : IGBT Module

Type Name : 7MBR75SB060-01

Spec. No. : MS6M 0552

Date : Jun. - 02 - 2000

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Matsumoto Factory

				Fuji Electric Co., Ltd.	
	DATE	NAME	APPROVED		
DRAWN	Jun. - 2 - 00	<i>T. Kobayashi</i>		DWG. NO.	MS6M 0552
CHECKED	June - 2 - 00	<i>S. Kato</i>	<i>T. Nishida</i>		

H04-004-05

# Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jun. - 2 - '60	enactment	—	—	Issued date	—	S. Muta	T. Miyasaka

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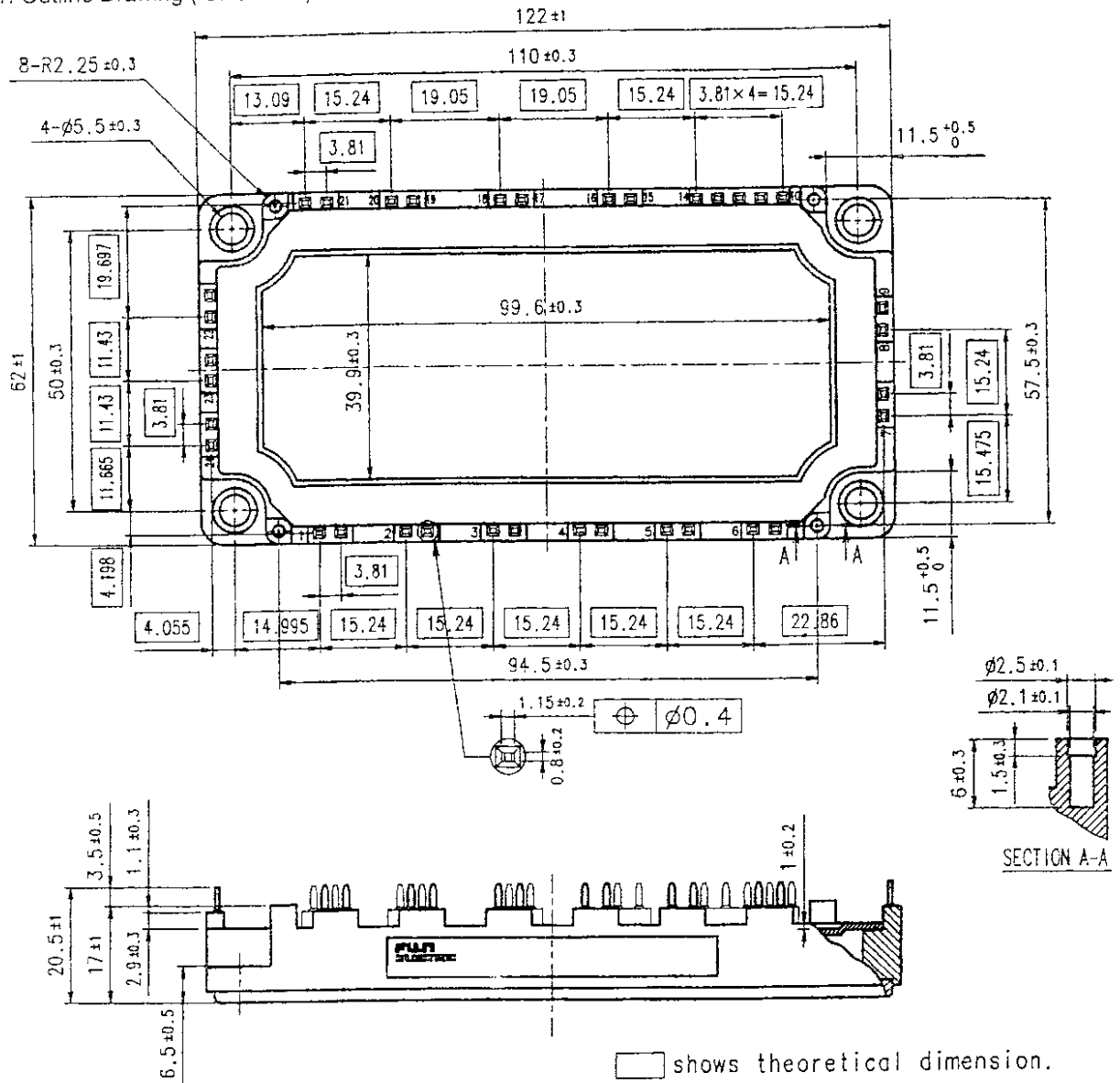
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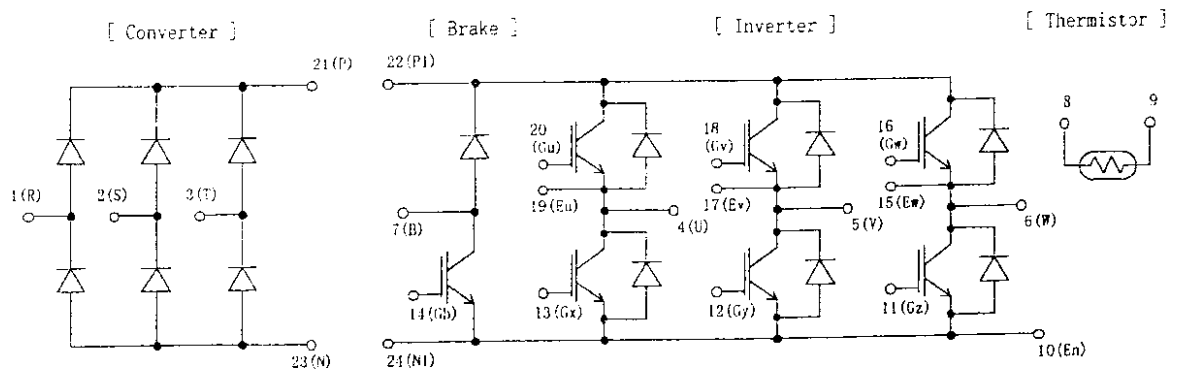
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# 7MBR75SB060-01

## 1. Outline Drawing ( Unit : mm )



## 2. Equivalent circuit



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3. Absolute Maximum Ratings ( at Tc= 25°C unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units
Inverter	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		±20	V
	Collector current	Ic	Continuous	75	A
		Icp	1ms	50	A
		-Ic		75	A
Collector Power Dissipation	Pc	1 device	300	W	
Brake	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		±20	V
	Collector current	Ic	Continuous	50	A
		Icp	1ms	100	A
	Collector Power Dissipation	Pc	1 device	200	W
Repetitive peak reverse Voltage(Diode)	VRRM		600	V	
Converter	Repetitive peak reverse Voltage	VRRM		800	V
	Average Output Current	Io	50Hz/60Hz sine wave	75	A
	Surge Current (Non-Repetitive)	IFSM	Tj=150°C, 10ms	525	A
	I <sup>2</sup> t (Non-Repetitive)	I <sup>2</sup> t	half sine wave	1378	A <sup>2</sup> s
Junction temperature		Tj		150	°C
Storage temperature		Tstg		-40~ +125	°C
Isolation voltage	between terminal and copper base <sup>(*)</sup>	Viso	AC : 1min.	2500	V
	between thermistor and others <sup>(*)</sup>			2500	V
Mounting Screw Torque <sup>(*)</sup>				3.5	N·m

(\*1) All terminals should be connected together when isolation test will be done.

(\*2) Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(\*3) Recommendable Value : 2.5~3.5 N·m (M5)

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4. Electrical characteristics ( at Tj= 25C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	Max.			
Inverter	Zero gate voltage Collector current	ICES	VGE 0 V, VCE 600 V			1.0	mA	
	Gate-Emitter leakage current	IGES	VCE 0 V, VGE +20 V			200	nA	
	Gate-Emitter threshold voltage	VGE(th)	VCE 20 V, Ic = 75 m	5.5	7.8	8.5	V	
	Collector-Emitter saturation voltage	VCE(sat)	VGE 15 V, chip		1.8			V
			Ic = 75 A, terminal		2.1	2.55		
	Input capacitance	Cies	VGE 0 V, VCE 10 V f = 1 MHz		7500			pF
	Turn-on time	ton	Vcc= 300 V		0.45	1.2		us
		tr	Ic = 75 A		0.25	0.6		
		tr(0)	VGE +-15 V		0.08			
	Turn-off time	toff	RG = 33 ohm		0.40	1.0		
tf				0.05	0.35			
Forward on voltage	VF	IF = 75 A	chip		1.7		V	
			terminal		2.0	2.7		
Reverse recovery time	trr	IF = 75 A				300	ns	
Brake	Zero gate voltage Collector current	ICES	VGE 0 V, VCE 600 V			1.0	mA	
	Gate-Emitter leakage current	IGES	VCE 0 V, VGE +20 V			200	nA	
	Collector-Emitter saturation voltage	VCE(sat)	VGE 15 V, chip		1.8			V
			Ic = 50 A, terminal		2.05	2.5		
	Turn-on time	ton	Vcc= 300 V		0.45	1.2		us
		tr	Ic = 50 A		0.25	0.6		
	Turn-off time	toff	VGE +-15 V		0.40	1.0		
		tf	RG = 51 ohm		0.05	0.35		
	Reverse current	IRRM	VR = 600 V				1.0	mA
	Converter	Forward on voltage	VFM	IF = 75 A	chip		1.1	
terminal						1.2	1.5	
Reverse current	IRRM	VR = 800 V				1.0	mA	
Thermistor	Resistance	R	T = 25C		5000		ohm	
			T = 100C	465	495	520		
	B value	B	T = 25/50C	3305	3375	3450	K	

5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.42	C/W
		Inverter FWD			0.90	
		Brake IGBT			0.63	
		Converter Diode			0.70	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (*)		0.05		C/W

\* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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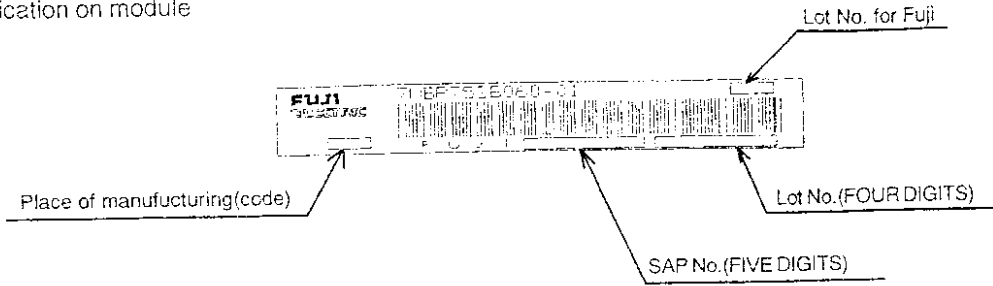
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6. Indication on module



7. Applicable category

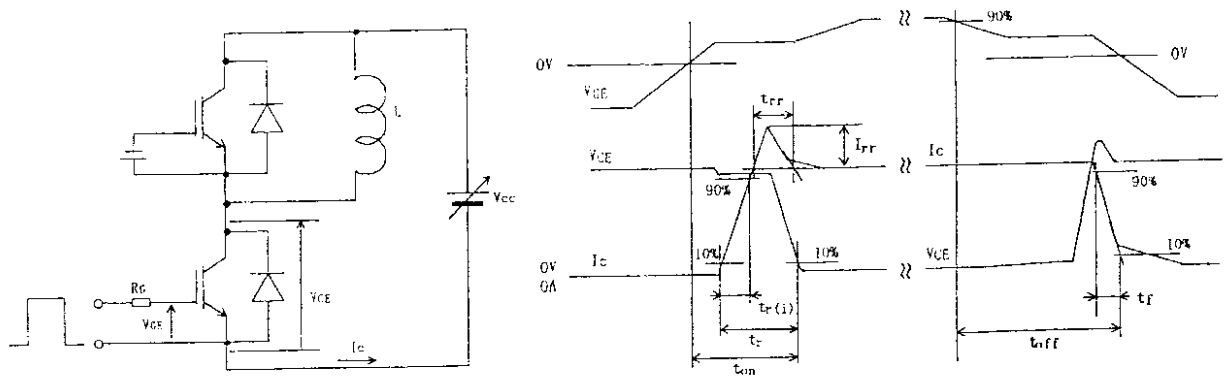
This specification is applied to Power Integrated Module named 7MBR75SB060-01.

8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

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9. Definitions of switching time



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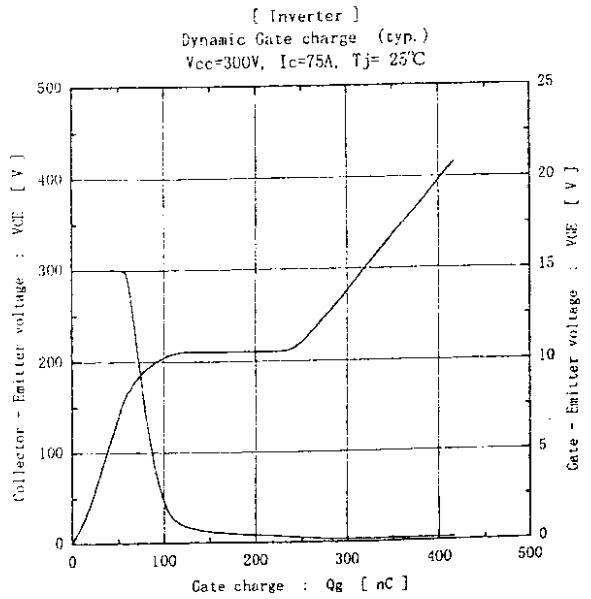
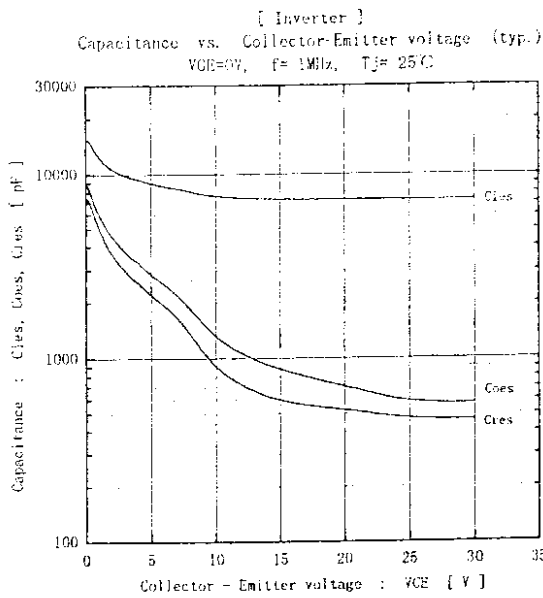
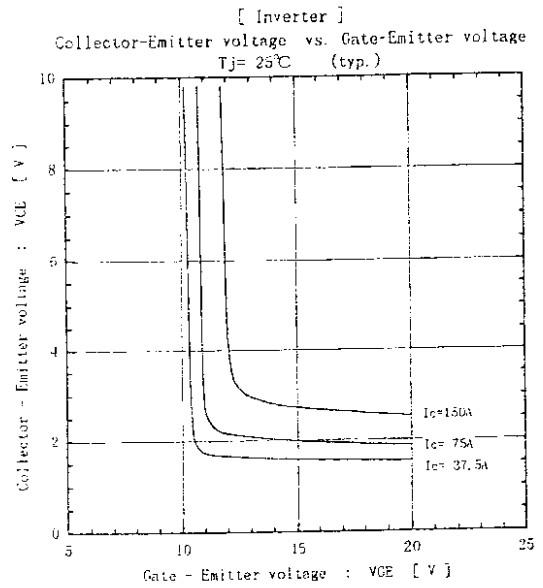
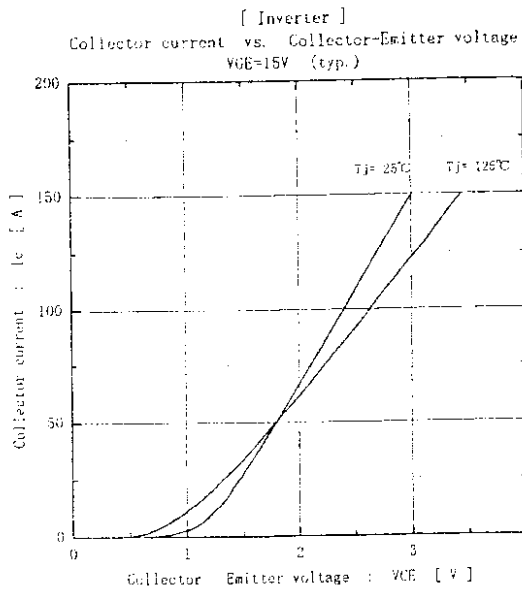
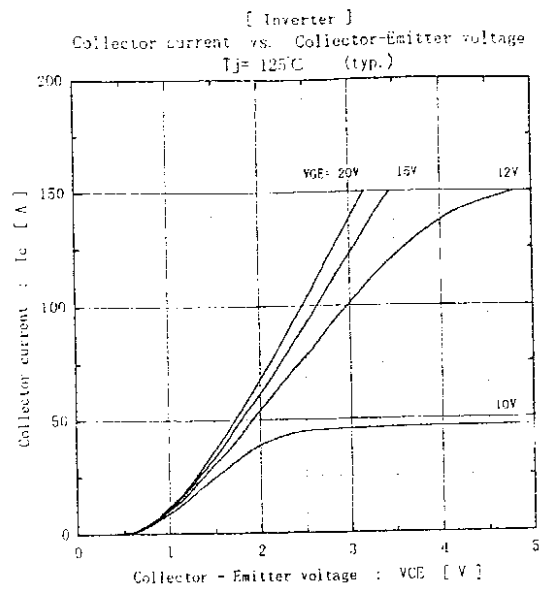
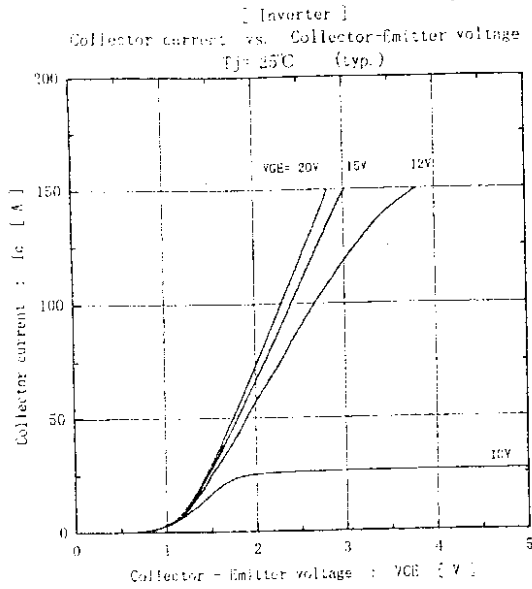
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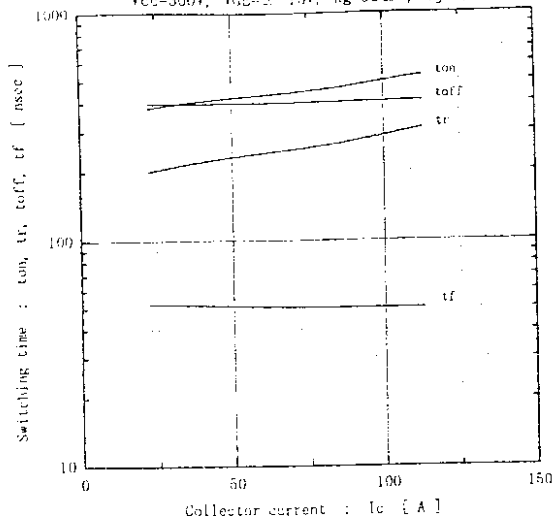
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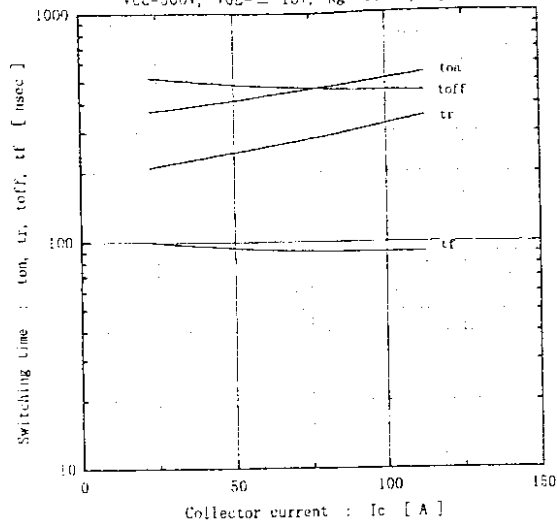
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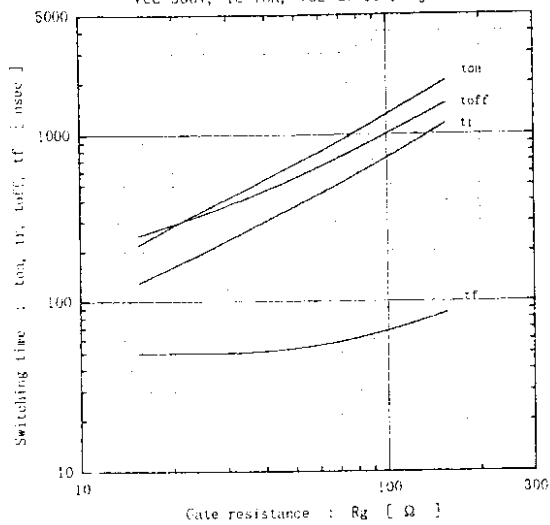
[ Inverter ]  
Switching time vs. Collector current (typ.)  
 $V_{CC}=300V, V_{GE}=\pm 15V, R_g=33\Omega, T_j=25^\circ C$



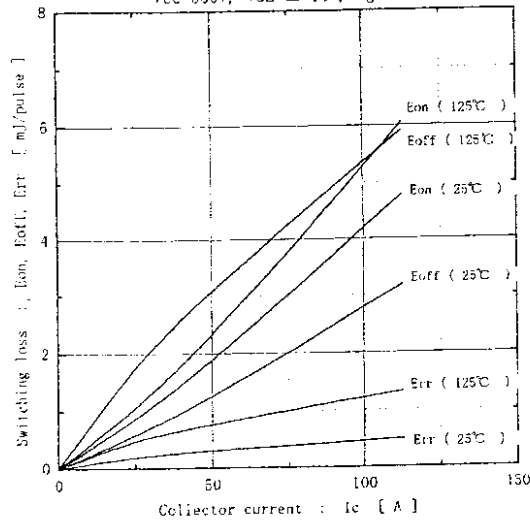
[ Inverter ]  
Switching time vs. Collector current (typ.)  
 $V_{CC}=300V, V_{GE}=\pm 15V, R_g=33\Omega, T_j=125^\circ C$



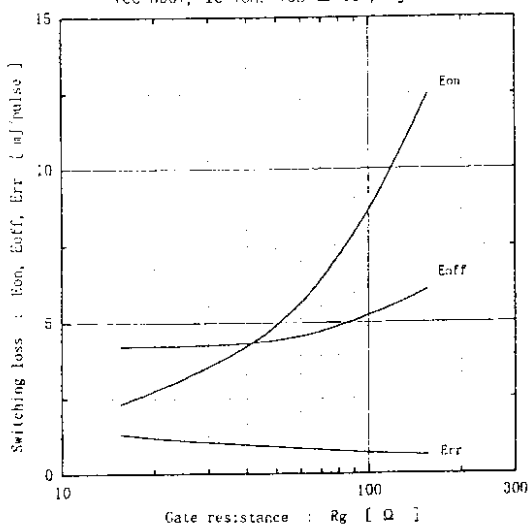
[ Inverter ]  
Switching time vs. Gate resistance (typ.)  
 $V_{CC}=300V, I_c=75A, V_{GE}=\pm 15V, T_j=25^\circ C$



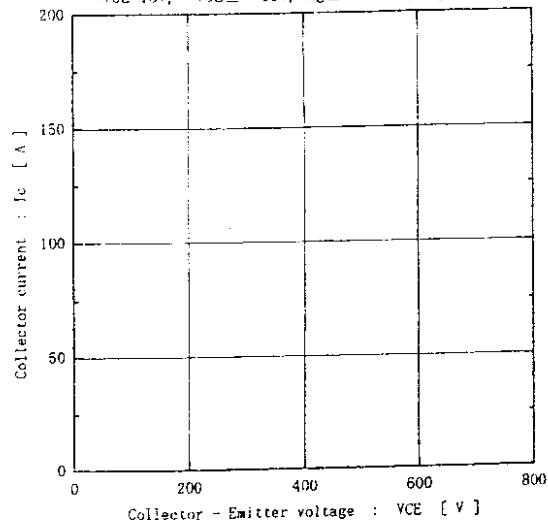
[ Inverter ]  
Switching loss vs. Collector current (typ.)  
 $V_{CC}=300V, V_{GE}=\pm 15V, R_g=33\Omega$



[ Inverter ]  
Switching loss vs. Gate resistance (typ.)  
 $V_{CC}=300V, I_c=75A, V_{GE}=\pm 15V, T_j=125^\circ C$



[ Inverter ]  
Reverse bias safe operating area  
 $+V_{CE}=15V, -V_{CE}\le 15V, R_g\ge 33\Omega, T_j\le 125^\circ C$



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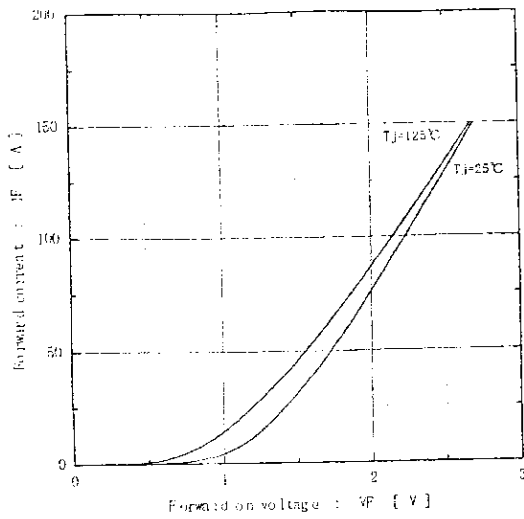
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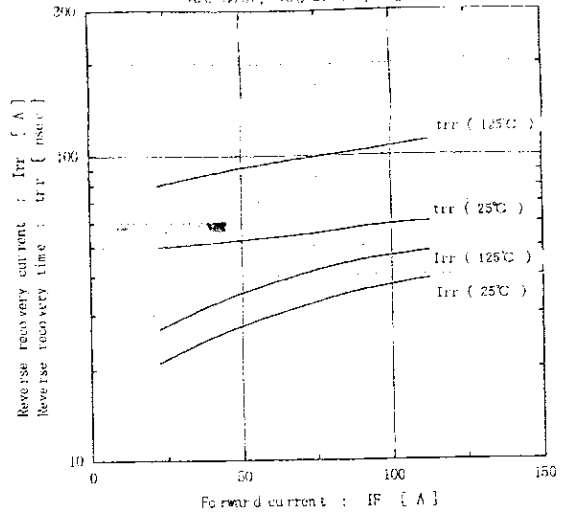


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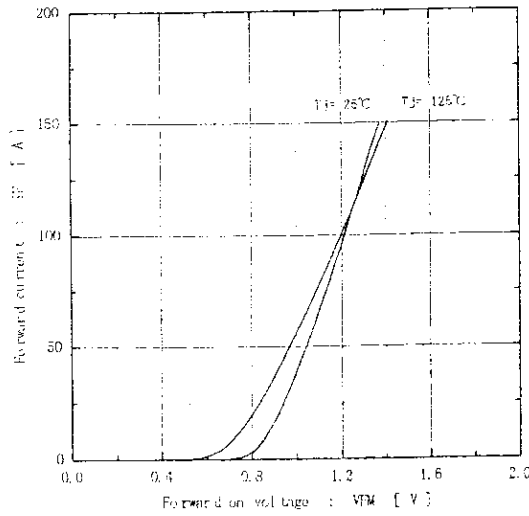
[ Inverter ]  
Forward current vs. Forward on voltage (typ.)



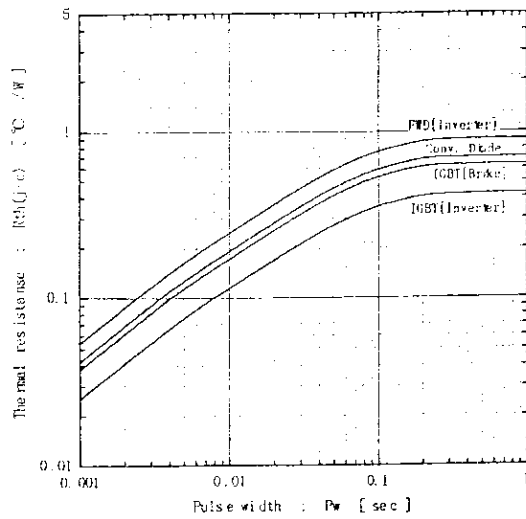
[ Inverter ]  
Reverse recovery characteristics (typ.)  
 $V_{CE} = 150V, V_{GE} \pm 15V, R_{\theta} = 23 \Omega$



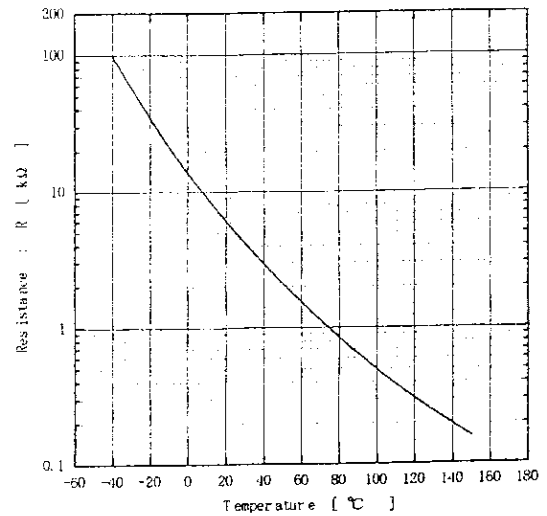
[ Converter ]  
Forward current vs. Forward on voltage (typ.)



Transient thermal resistance



[ Thermistor ]  
Temperature characteristic (typ.)



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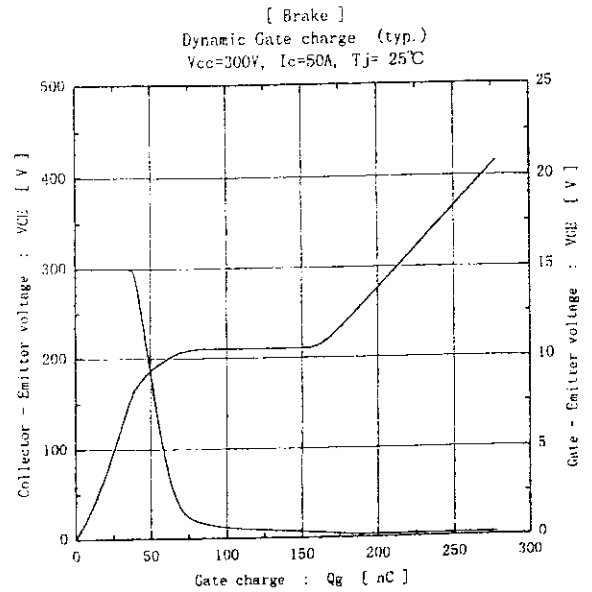
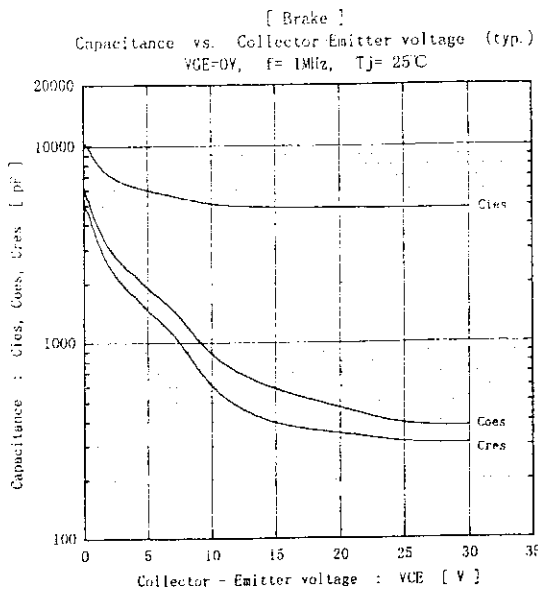
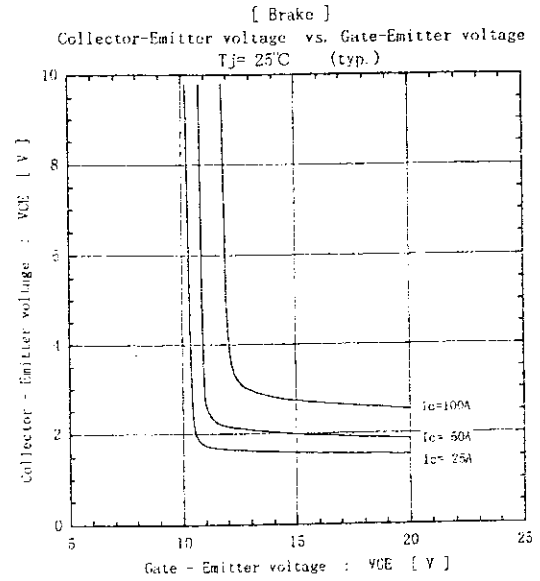
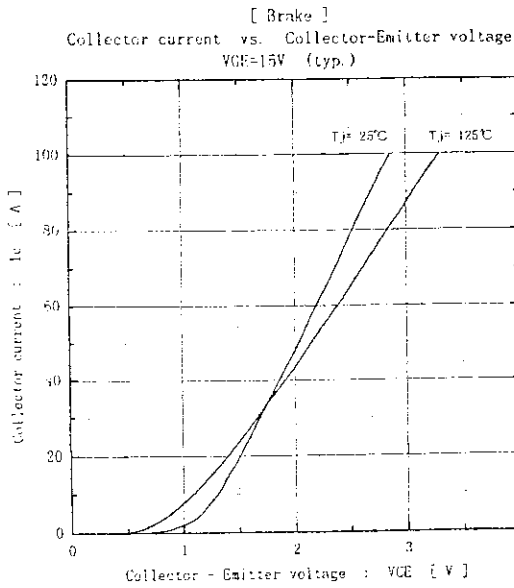
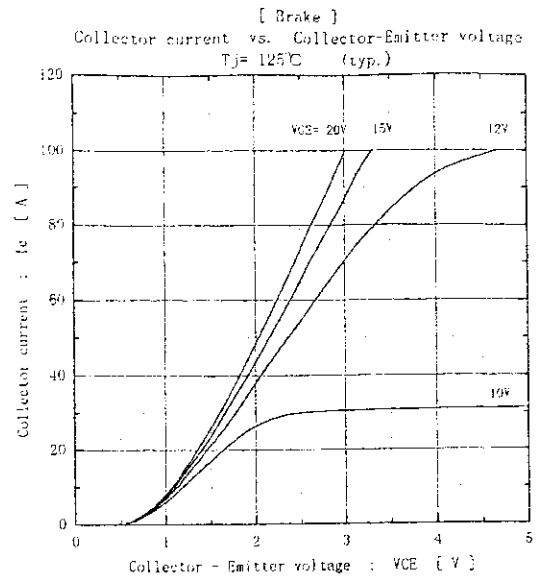
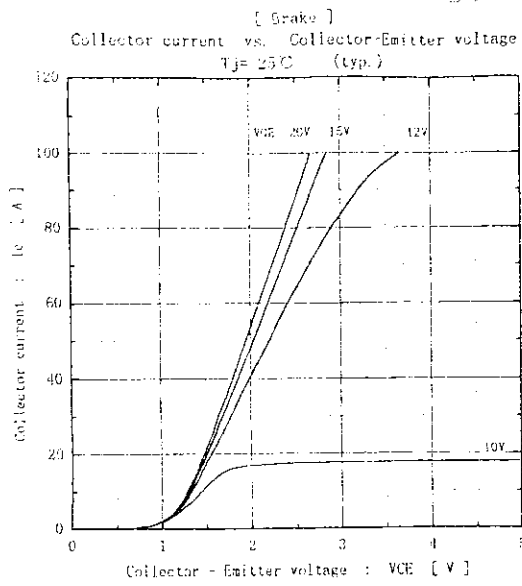
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